

## P-Channel Enhancement Mode MOSFET

### 1. Product Information

#### 1.1 Features

- Advanced trench cell design
- Low Thermal Resistance

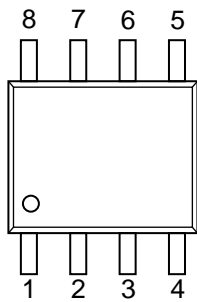
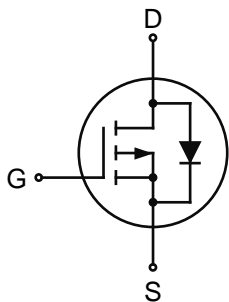
#### 1.2 Applications

- Motor drivers
- DC - DC Converter

#### 1.3 Quick reference

- $BV \geq -30\text{ V}$
- $R_{DS(ON)} \leq 14\text{ m}\Omega @ V_{GS} = -10\text{ V}$
- $P_{tot} \leq 20\text{ W}$
- $R_{DS(ON)} \leq 23\text{ m}\Omega @ V_{GS} = -4.5\text{ V}$
- $I_D \leq -15\text{ A}$

### 2. Pin Description

Pin	Description	Simplified Outline	Symbol
1,2,3	Source(S)		
4	Gate(G)		
5,6,7,8	Drain(D)		

Top View  
SOP-8

## 3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	Drain-Source Voltage	$T_C = 25\text{ }^\circ\text{C}$	-	-30	V
$V_{GS}$	Gate-Source Voltage	$T_C = 25\text{ }^\circ\text{C}$	-	$\pm 20$	V
$I_D^*$	Drain Current	$T_C = 25\text{ }^\circ\text{C}, V_{GS} = -10\text{ V}$	-	-15	A
$I_{DM}^{*,**,***}$	Pulsed Source Current	$T_C = 25\text{ }^\circ\text{C}, V_{GS} = -10\text{ V}$	-	-40	A
$P_{tot}^*$	Total Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	-	20	W
$T_{stg}$	Storage Temperature		-55	150	$^\circ\text{C}$
$T_J$	Junction Temperature		-	150	$^\circ\text{C}$
$I_S$	Diode Forward Current	$T_C = 25\text{ }^\circ\text{C}$	-	-26	A
$R_{\theta JC}^*$	Thermal Resistance- Junction to Ambient		-	6	$^\circ\text{C} / \text{W}$

Notes :

- \* Surface Mounted on 1 in<sup>2</sup> pad area,  $t \leq 10\text{ sec}$
- \*\* Pulse width  $\leq 10\text{ }\mu\text{s}$ , duty cycle  $\leq 1\%$
- \*\*\* Limited by bonding wire

## 4. Marking Information

Product Name	Marking
KJ12P03S	<div style="display: inline-block; border: 1px solid black; padding: 2px;"> <b>4407</b>  <b>YYWW</b> </div> <b>YYWW:</b> Date Code

## 5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
KJ12P03S	SOP-8			4000	

Note: KUAJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC / JEDEC J-STD-020C)

## 6. Electrical Characteristics (T<sub>C</sub> = 25 °C Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
B <sub>VDS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-30	-	-	V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>DS</sub> = -250 μA	-1.0	-	-2.0	V
I <sub>DSS</sub>	Zero Gate Voltage Source Current	V <sub>DS</sub> = -24 V, V <sub>GS</sub> = 0 V	-	-	-1	μA
		T <sub>J</sub> = 85 °C	-	-	-30	μA
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> = ± 20 V, V <sub>DS</sub> = 0 V	-	-	±100	nA
R <sub>DS(ON)</sub> <sup>a</sup>	Drain-Source On-State Resistance	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -20 A	-	11.5	14	mΩ
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -10 A	-	18	23	mΩ
<b>Diode Characteristics</b>						
V <sub>SD</sub> <sup>a</sup>	Diode Forward Voltage	I <sub>SD</sub> = -20 A, V <sub>GS</sub> = 0 V	-	-	-1.3	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>SD</sub> = -20 A, dI <sub>SD</sub> /dt = 100 A/μs	-	8.3	-	nS
Q <sub>rr</sub>	Reverse Recovery Charge		-	0.6	-	nC
<b>Dynamic Characteristics<sup>b</sup></b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = -15 V Frequency = 1 MHz	-	2628	-	pF
C <sub>oss</sub>	Output Capacitance		-	294	-	
C <sub>rss</sub>	Reverse Transfer Capacitance		-	271	-	
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> = -15 V, V <sub>GEN</sub> = -10 V, R <sub>G</sub> = 4.5 Ω, R <sub>L</sub> = 0.75 Ω, I <sub>D</sub> = -20 A	-	9	-	nS
t <sub>r</sub>	Turn-on Rise Time		-	8	-	
t <sub>d(off)</sub>	Turn-off Delay Time		-	28	-	
t <sub>f</sub>	Turn-off Fall Time		-	10	-	
<b>Gate Charge Characteristics<sup>b</sup></b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> = -10 V, V <sub>DS</sub> = -15 V, I <sub>DS</sub> = -20 A	-	55.3	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	7.9	-	
Q <sub>gd</sub>	Gate-Drain Charge		-	11.3	-	

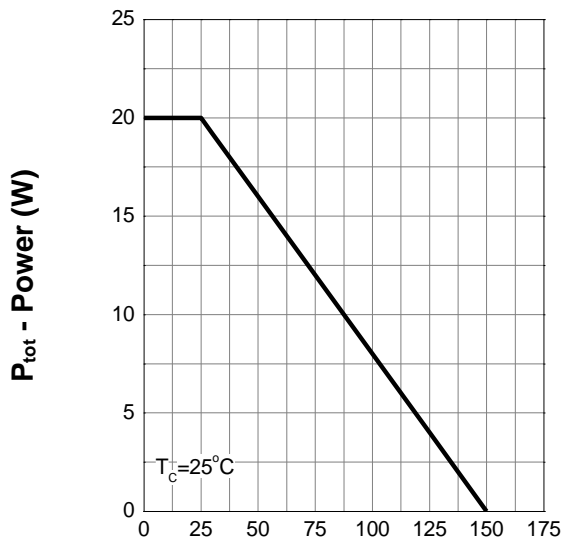
Notes :

a : Pulse test ; pulse width ≤ 300 μs, duty cycle ≤ 2 %

b : Guaranteed by design, not subject to production testing

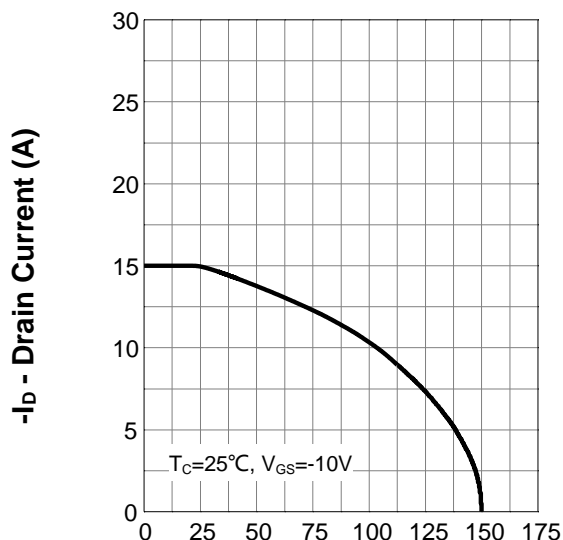
## 7. Typical Characteristics

**Power Capability**



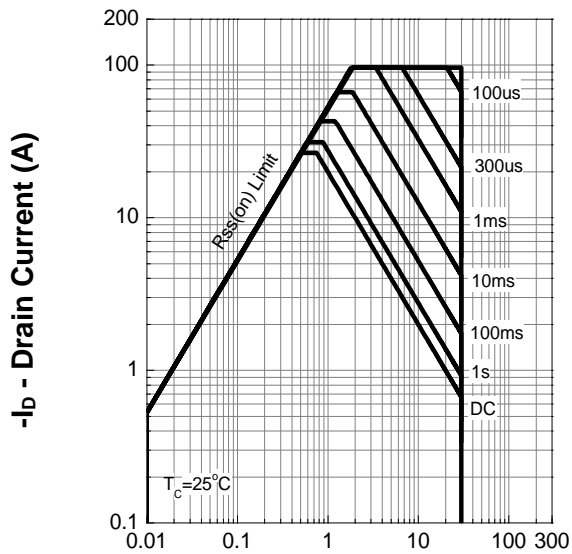
T<sub>j</sub> - Junction Temperature (°C)

**Current Capability**



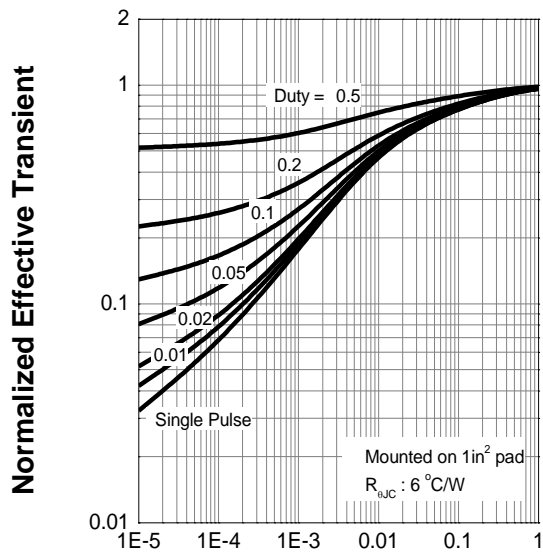
T<sub>j</sub> - Junction Temperature (°C)

**Safe Operation Area**



-V<sub>DS</sub> - Drain-Source Voltage (V)

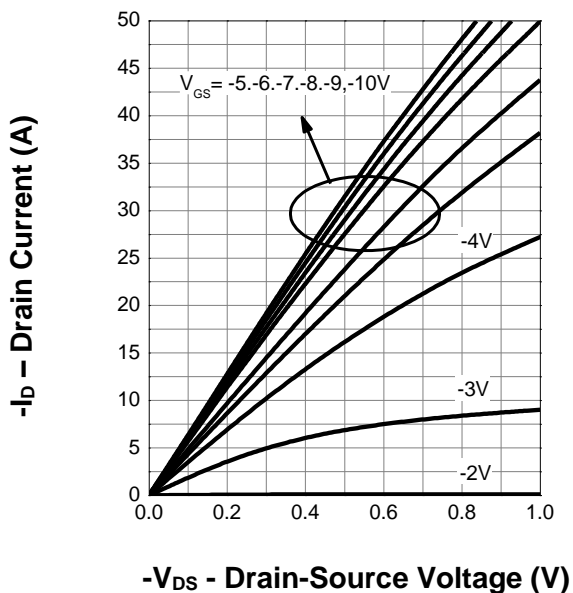
**Thermal Transient Impedance**



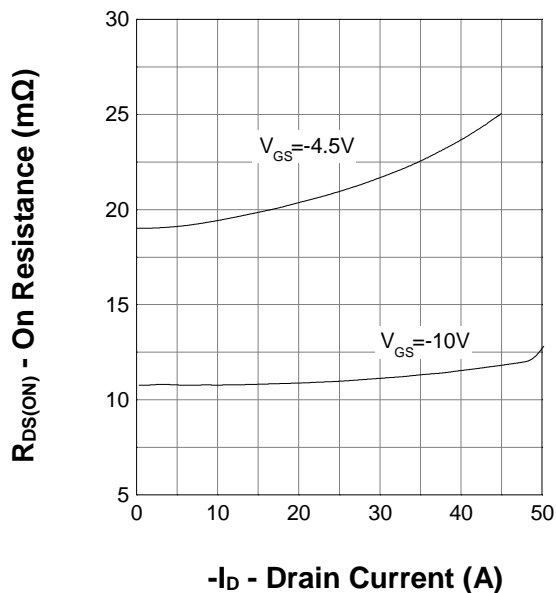
Square Wave Pulse Duration (sec)

## 7. Typical Characteristics (cont.)

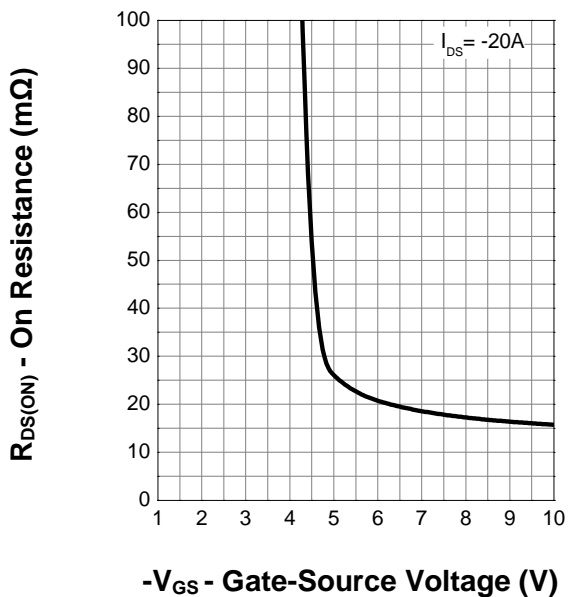
Output Characteristics



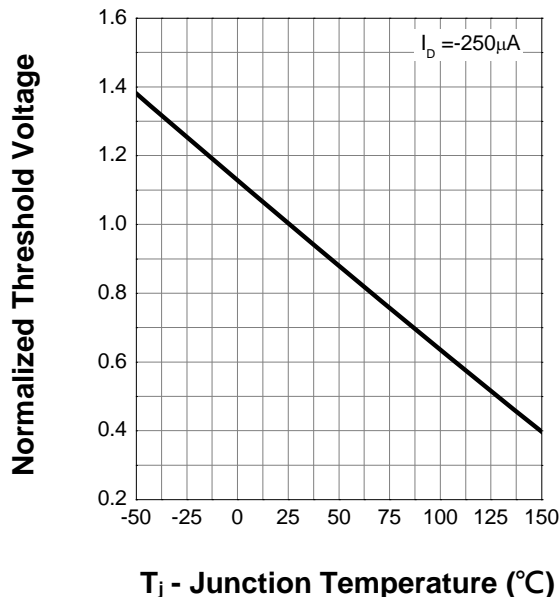
Drain-Source On Resistance



Transfer Characteristics

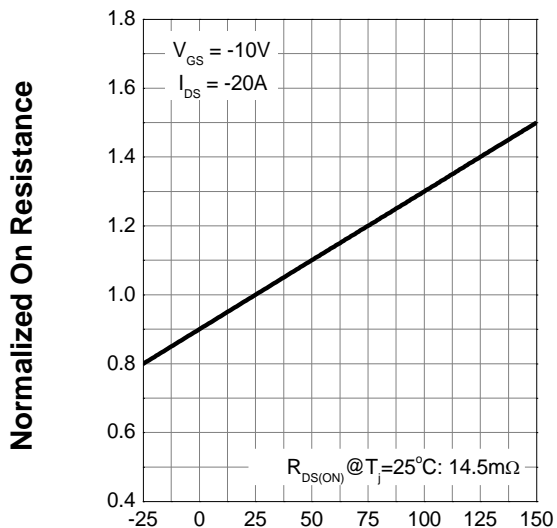


Gate Threshold Voltage

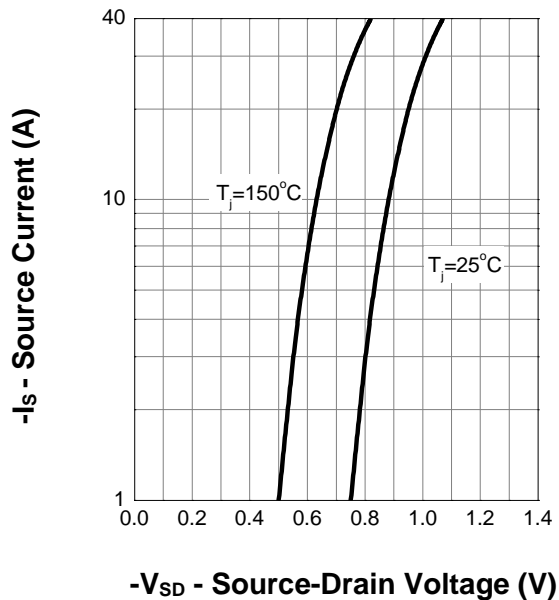


## 7. Typical Characteristics (cont.)

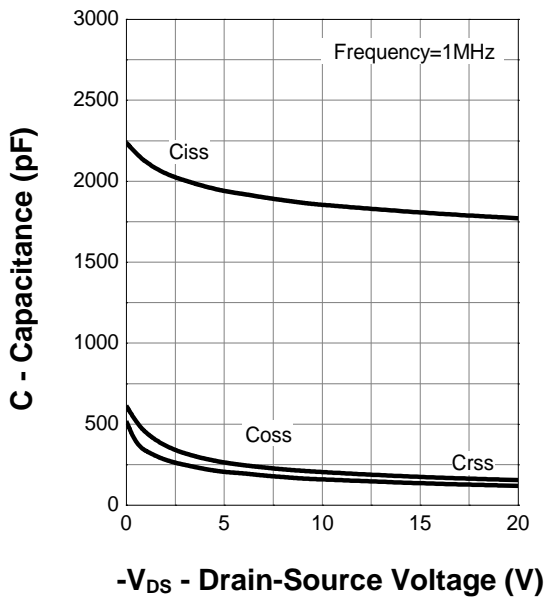
**Drain-Source On Resistance**



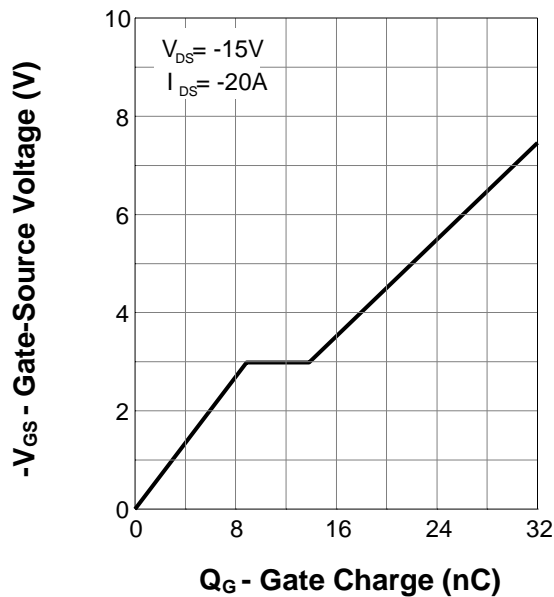
**Body Diode Characteristics**



**Capacitance**

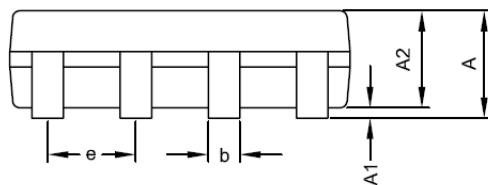
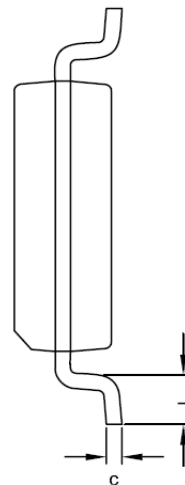
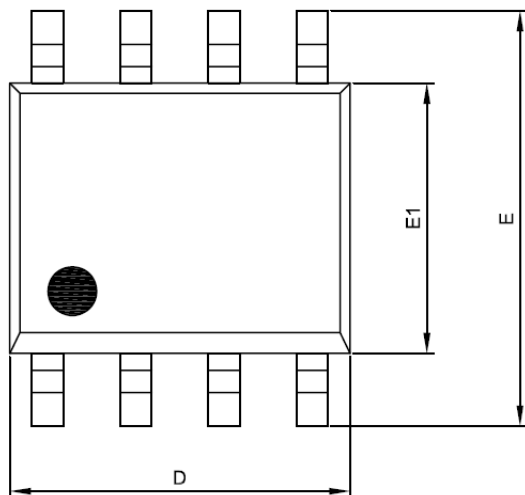


**Gate Charge**



## 8. Package Dimensions

### SOP-8 Package



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	1.35	1.75
A1	0.00	0.25
A2	1.15	1.50
D	4.80	5.00
E	5.80	6.20
E1	3.80	4.00
c	0.19	0.27
b	0.33	0.53
e	1.27 BSC	
L	0.40	1.27